NJX1675PDR2G

Complementary 30 V, 6.0 A, Transistor

These devices are designed for use in low voltage, high speed switching applications where affordable efficient energy control is important.

Typical applications are low voltage motor controls in mass storage products such as disc drives and tape drives. In the automotive industry they can be used in air bag deployment and in the instrument cluster.

Features

- These Devices are Pb−Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS (T_A = 25°C)

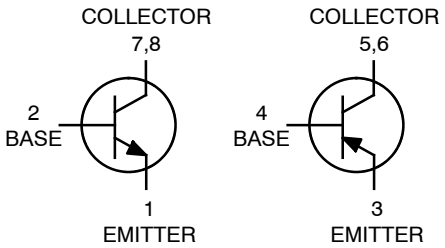
Rating		Symbol	Max	Unit
Collector-Emitter Voltage	NPN PNP	V_{CEO}	30 −30	Vdc
Collector-Base Voltage	NPN PNP	V_{CBO}	30 −30	Vdc
Emitter-Base Voltage	NPN PNP	V_{EBO}	6.0 −7.0	Vdc
Collector Current − Continuous	NPN PNP	I_C	3.0 −3.0	A
Collector Current − Peak	NPN PNP	I_{CM}	6.0 −6.0	A
Electrostatic Discharge		ESD	HBM Class 3B MM Class C	

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

ON Semiconductor®

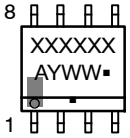
http://onsemi.com

30 VOLTS, 6.0 AMPS COMPLEMENTARY TRANSISTOR EQUIVALENT $R_{DS(on)}$ 80 mΩ



SOIC−8
CASE 751
STYLE 16

DEVICE MARKING



XXXXXX = Specific Device Code
A = Assembly Location
Y = Year
WW = Work Week
▪ = Pb−Free Package
(Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping†
NJX1675PDR2G	SOIC−8 (Pb−Free)	2500 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation (Note 1) T_A = 25°C Derate above 25°C	P_D	2.0 16	W mW/°C
Thermal Resistance, Junction-to-Ambient (Note 1)	$R_{\theta JA}$	62	°C/W
Junction and Storage Temperature Range	T_J, T_{stg}	-55 to +150	°C

1. FR-4 @ 100 mm^2, 1 oz. copper traces, still air, t ≤ 10 sec.
2. Dual heated values assume total power is the sum of two equally powered devices.

NPN ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector - Emitter Breakdown Voltage (I_C = 10 mAdc, I_B = 0)	$V_{(BR)CEO}$	30	-	-	Vdc
Collector - Base Breakdown Voltage (I_C = 0.1 mAdc, I_E = 0)	$V_{(BR)CBO}$	30	-	-	Vdc
Emitter - Base Breakdown Voltage (I_E = 1.0 mAdc, I_C = 0)	$V_{(BR)EBO}$	6.0	-	-	Vdc
Collector Cutoff Current (V_{CB} = 30 Vdc, I_E = 0)	I_{CBO}	-	-	0.1	μAdc
Emitter Cutoff Current (V_{EB} = 5.0 Vdc)	I_{EBO}	-	-	0.1	μAdc
ON CHARACTERISTICS					
DC Current Gain (Note 4) (I_C = 10 mA, V_{CE} = 2.0 V) (I_C = 500 mA, V_{CE} = 2.0 V) (I_C = 1.0 A, V_{CE} = 2.0 V) (I_C = 2.0 A, V_{CE} = 2.0 V)	h_{FE}	 100 100 180 180	 400 350 340 320	 - - - -	
Collector - Emitter Saturation Voltage (Note 4) (I_C = 0.1 A, I_B = 0.010 A) (I_C = 1.0 A, I_B = 0.100 A) (I_C = 1.0 A, I_B = 0.010 A) (I_C = 2.0 A, I_B = 0.200 A)	$V_{CE(sat)}$	 - - - -	 0.008 0.044 0.080 0.082	 0.011 0.060 0.115 0.115	V
Base - Emitter Saturation Voltage (Note 4) (I_C = 1.0 A, I_B = 0.01 A)	$V_{BE(sat)}$	-	0.780	0.900	V
Base - Emitter Turn-on Voltage (Note 4) (I_C = 0.1 A, V_{CE} = 2.0 V)	$V_{BE(on)}$	-	0.650	0.750	V
Cutoff Frequency (I_C = 100 mA, V_{CE} = 5.0 V, f = 100 MHz)	f_T	100	-	-	MHz
Input Capacitance (V_{EB} = 0.5 V, f = 1.0 MHz)	Cibo	-	320	450	pF
Output Capacitance (V_{CB} = 3.0 V, f = 1.0 MHz)	Cobo	-	40	-	pF
SWITCHING CHARACTERISTICS					
Delay (V_{CC} = 30 V, I_C = 750 mA, I_{B1} = 15 mA)	t_d	-	-	100	ns
Rise (V_{CC} = 30 V, I_C = 750 mA, I_{B1} = 15 mA)	t_r	-	-	100	ns
Storage (V_{CC} = 30 V, I_C = 750 mA, I_{B1} = 15 mA)	t_s	-	-	780	ns
Fall (V_{CC} = 30 V, I_C = 750 mA, I_{B1} = 15 mA)	t_f	-	-	110	ns

3. Pulsed Condition: Pulse Width = 300 μsec, Duty Cycle ≤ 2%.

PNP ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector – Emitter Breakdown Voltage (I_C = −10 mAdc, I_B = 0)	$V_{(BR)CEO}$	−30	–	–	Vdc
Collector – Base Breakdown Voltage (I_C = −0.1 mAdc, I_E = 0)	$V_{(BR)CBO}$	−30	–	–	Vdc
Emitter – Base Breakdown Voltage (I_E = −1.0 mAdc, I_C = 0)	$V_{(BR)EBO}$	−7.0	–	–	Vdc
Collector Cutoff Current (V_{CB} = −30 Vdc, I_E = 0)	I_{CBO}	–	–	−0.1	μAdc
Emitter Cutoff Current (V_{EB} = −5.0 Vdc)	I_{EBO}	–	–	−0.1	μAdc
ON CHARACTERISTICS					
DC Current Gain (Note 4) (I_C = −10 mA, V_{CE} = −2.0 V) (I_C = −500 mA, V_{CE} = −2.0 V) (I_C = −1.0 A, V_{CE} = −2.0 V) (I_C = −2.0 A, V_{CE} = −2.0 V)	h_{FE}	 100 100 180 150	 380 340 300 230	 – – – –	
Collector – Emitter Saturation Voltage (Note 4) (I_C = −0.1 A, I_B = −0.010 A) (I_C = −1.0 A, I_B = −0.100 A) (I_C = −1.0 A, I_B = −0.010 A) (I_C = −2.0 A, I_B = −0.200 A)	$V_{CE(sat)}$	 – – – –	 −0.013 −0.075 −0.130 −0.135	 −0.017 −0.095 −0.170 −0.170	V
Base – Emitter Saturation Voltage (Note 4) (I_C = −1.0 A, I_B = −0.01 A)	$V_{BE(sat)}$	–	−0.780	−0.900	V
Base – Emitter Turn−on Voltage (Note 4) (I_C = −0.1 A, V_{CE} = −2.0 V)	$V_{BE(on)}$	–	−0.660	−0.750	V
Cutoff Frequency (I_C = −100 mA, V_{CE} = −5.0 V, f = 100 MHz)	f_T	100	120	–	MHz
Input Capacitance (V_{EB} = −0.5 V, f = 1.0 MHz)	Cibo	–	250	300	pF
Output Capacitance (V_{CB} = −3.0 V, f = 1.0 MHz)	Cobo	–	50	–	pF
SWITCHING CHARACTERISTICS					
Delay (V_{CC} = −30 V, I_C = −750 mA, I_{B1} = −15 mA)	t_d	–	–	60	ns
Rise (V_{CC} = −30 V, I_C = −750 mA, I_{B1} = −15 mA)	t_r	–	–	120	ns
Storage (V_{CC} = −30 V, I_C = −750 mA, I_{B1} = −15 mA)	t_s	–	–	400	ns
Fall (V_{CC} = −30 V, I_C = −750 mA, I_{B1} = −15 mA)	t_f	–	–	130	ns

4. Pulsed Condition: Pulse Width = 300 μsec, Duty Cycle ≤ 2%.

NPN TYPICAL CHARACTERISTICS

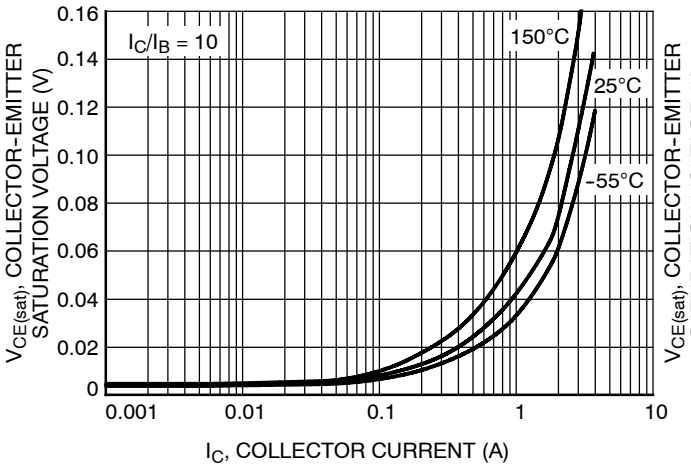


Figure 1. Collector Emitter Saturation Voltage vs. Collector Current

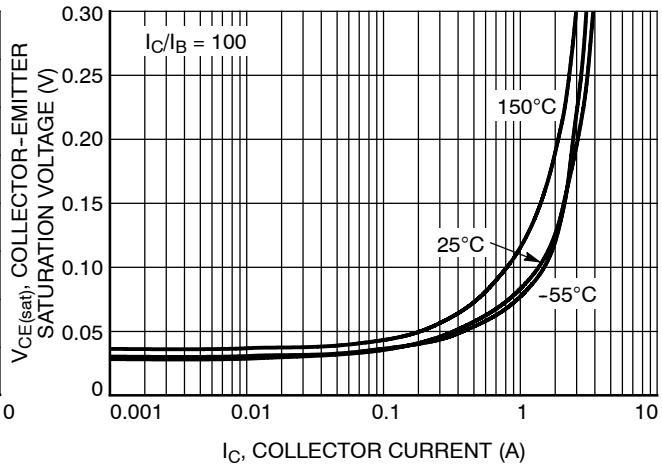


Figure 2. Collector Emitter Saturation Voltage vs. Collector Current

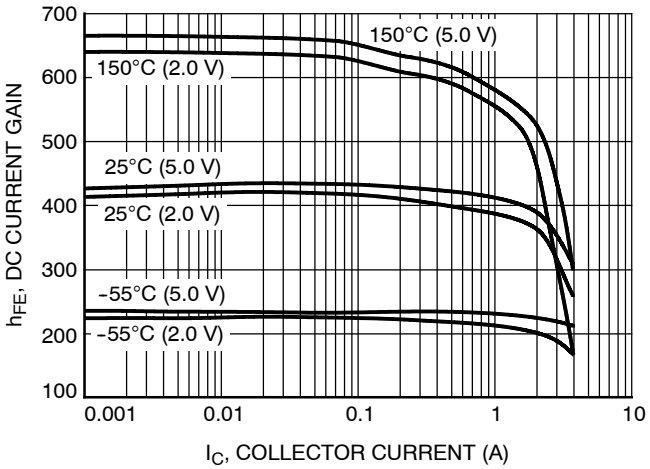


Figure 3. DC Current Gain vs. Collector Current

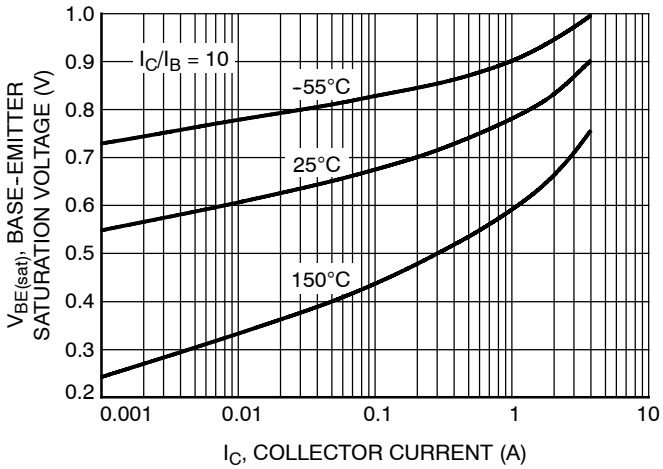


Figure 4. Base Emitter Saturation Voltage vs. Collector Current

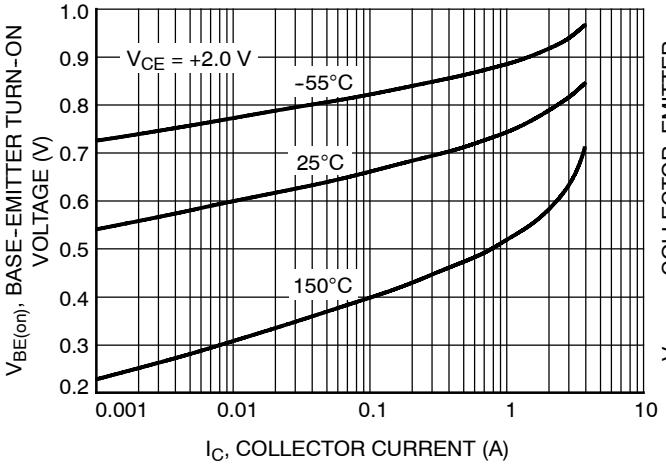


Figure 5. Base Emitter Turn−On Voltage vs. Collector Current

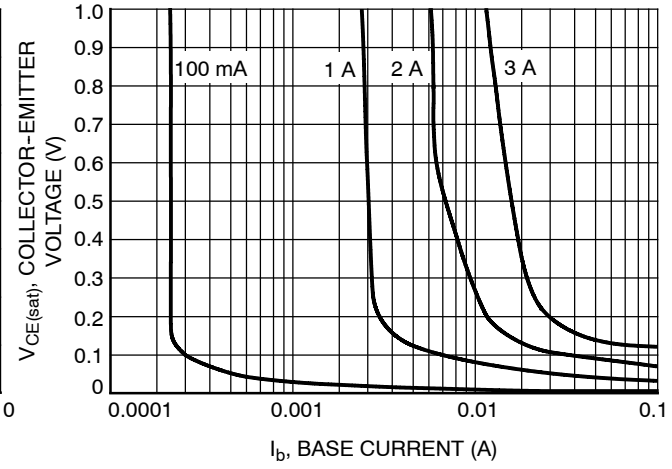


Figure 6. Saturation Region

NPN TYPICAL CHARACTERISTICS

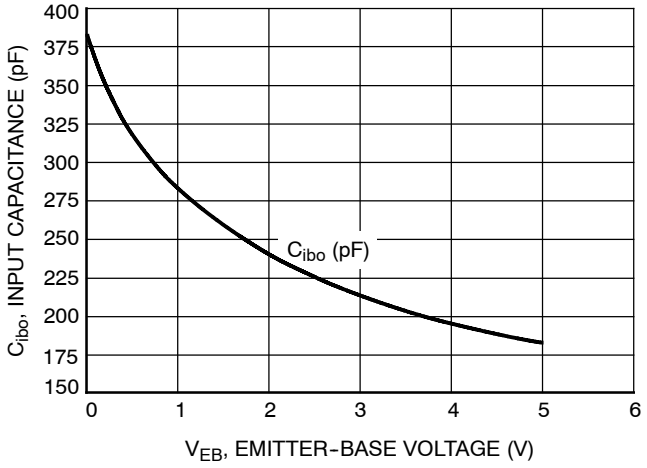


Figure 7. Input Capacitance

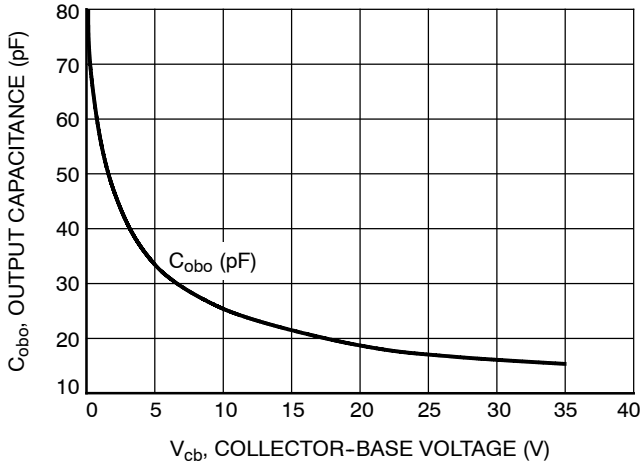


Figure 8. Output Capacitance

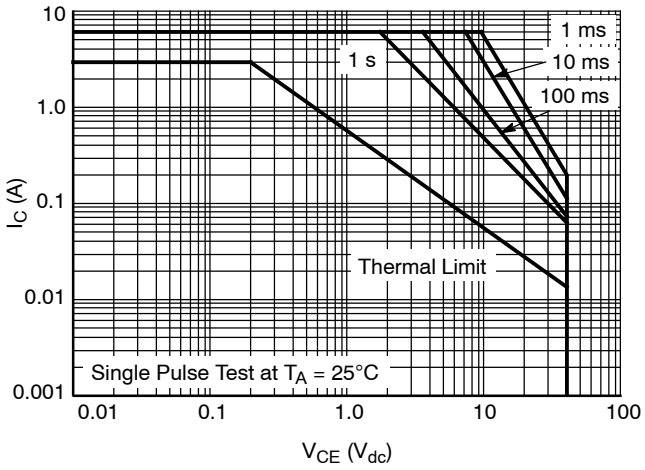


Figure 9. Safe Operating Area

PNP TYPICAL CHARACTERISTICS

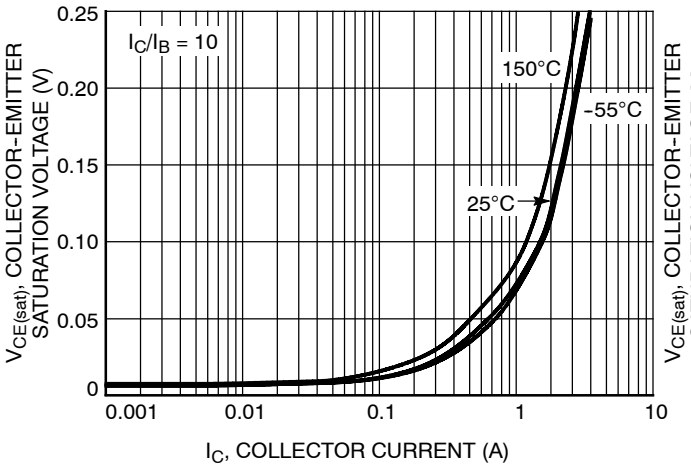


Figure 10. Collector Emitter Saturation Voltage vs. Collector Current

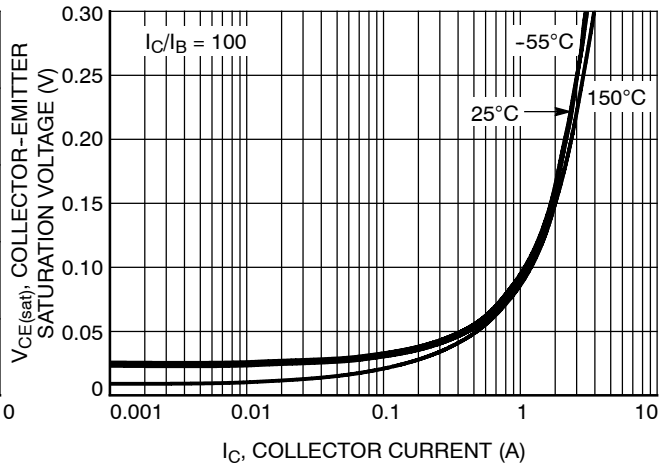


Figure 11. Collector Emitter Saturation Voltage vs. Collector Current

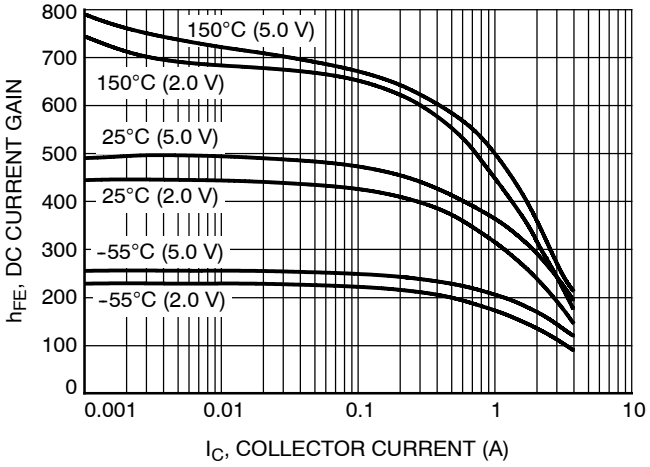


Figure 12. DC Current Gain vs. Collector Current

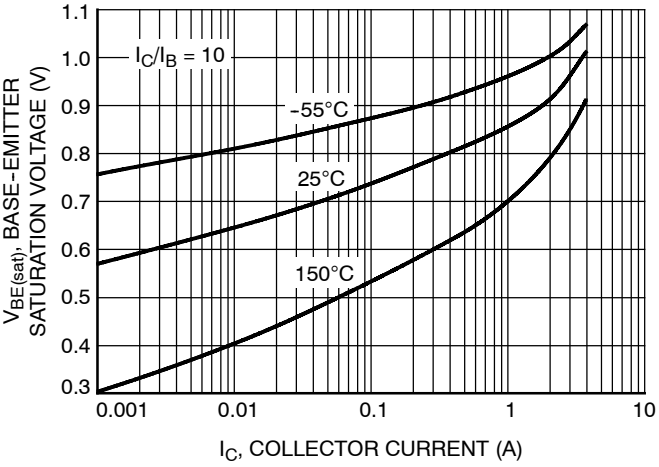


Figure 13. Base Emitter Saturation Voltage vs. Collector Current

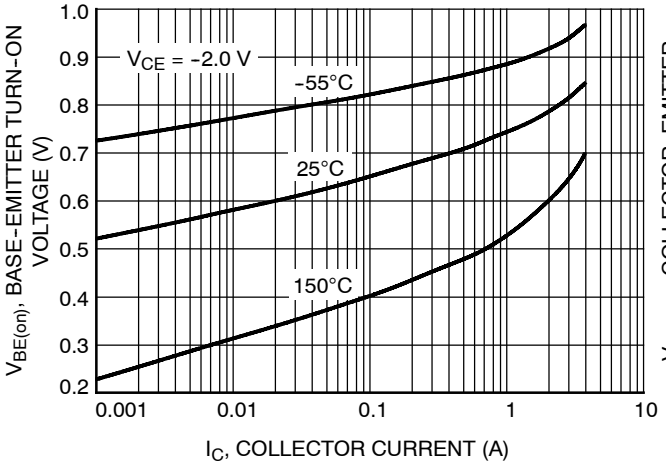


Figure 14. Base Emitter Turn−On Voltage vs. Collector Current

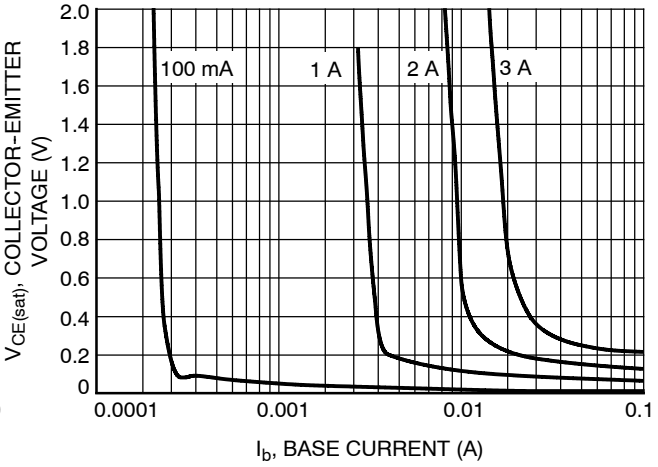


Figure 15. Saturation Region

PNP TYPICAL CHARACTERISTICS

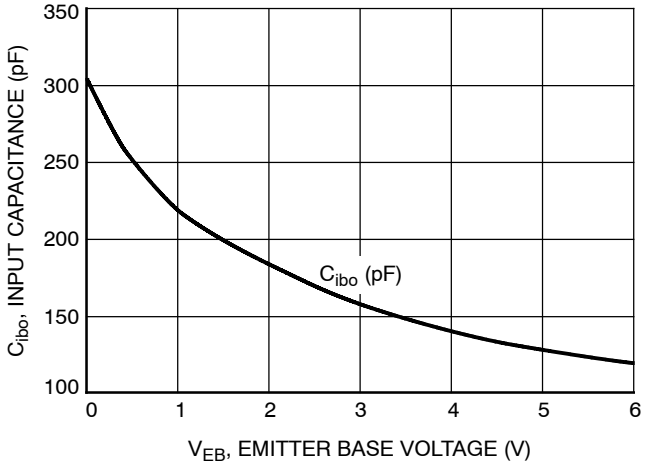


Figure 16. Input Capacitance

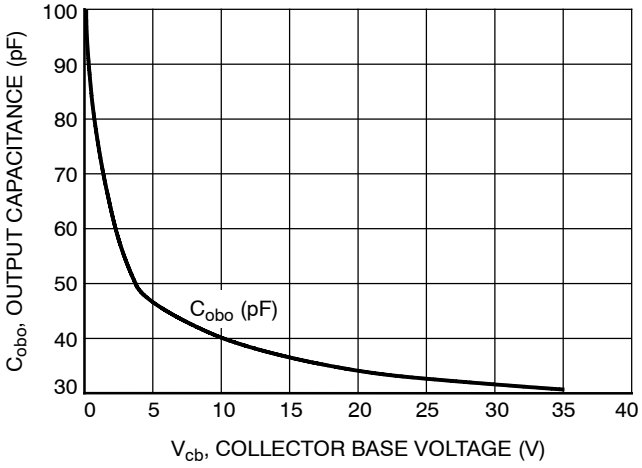


Figure 17. Output Capacitance

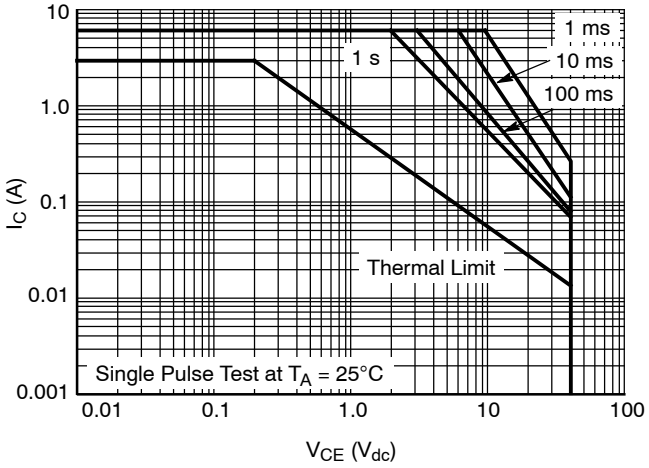
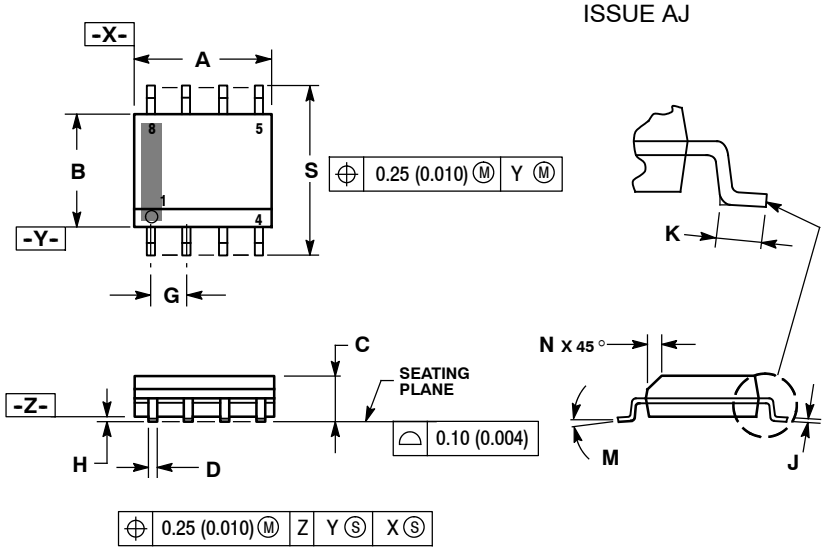


Figure 18. Safe Operating Area

NJX1675PDR2G

PACKAGE DIMENSIONS

SOIC−8 NB
CASE 751−07
ISSUE AJ

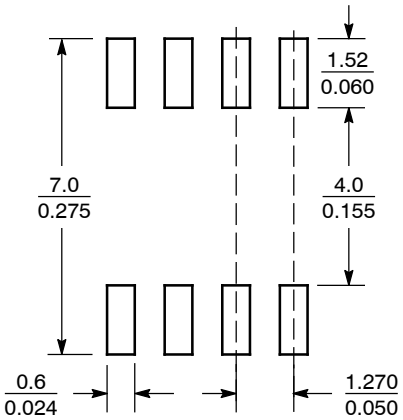


NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION A AND B DO NOT INCLUDE MOLD PROTRUSION.
4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
5. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.
6. 751−01 THRU 751−06 ARE OBSOLETE. NEW STANDARD IS 751−07.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
A	4.80	5.00	0.189	0.197
B	3.80	4.00	0.150	0.157
C	1.35	1.75	0.053	0.069
D	0.33	0.51	0.013	0.020
G	1.27 BSC		0.050 BSC	
H	0.10	0.25	0.004	0.010
J	0.19	0.25	0.007	0.010
K	0.40	1.27	0.016	0.050
M	0 °	8 °	0 °	8 °
N	0.25	0.50	0.010	0.020
S	5.80	6.20	0.228	0.244

STYLE 16:
PIN 1. EMITTER, DIE #1
2. BASE, DIE #1
3. EMITTER, DIE #2
4. BASE, DIE #2
5. COLLECTOR, DIE #2
6. COLLECTOR, DIE #2
7. COLLECTOR, DIE #1
8. COLLECTOR, DIE #1

SOLDERING FOOTPRINT*



SCALE 6:1 (mm / inches)

*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
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